

Page 3, ✓ line 11, ✓ change "the" to --an--;
line 16, ✓ change "13a" to --10a--.

IN THE CLAIMS

Please amend claims 1 and 3 as follows:

- fig. 1
Date 5/1
1. A semiconductor device, comprising:
a semiconductor substrate having a main surface;
an element isolating [isolation] region for defining an element forming region on the main surface of said semiconductor substrate;
an isolation region provided in a strip-shape and having a peak impurity concentration at a prescribed depth position from the main surface of said semiconductor substrate;
a connection hole provided piercing through said element isolating region;
an anti-HF (hydrofluoric acid) side wall film not etched by hydrofluoric acid, provided to cover a side wall of said connection hole at least near a lower end of said connection hole;
an interconnection layer provided to fill an inner portion of said connection hole; and